November 2006



# MMBT4401K

NPN Epitaxial Silicon Transistor

# **Switching Transistor**



1. Base 2. Emitter 3. Collector

# Absolute Maximum Ratings $T_a = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Value	Units	
V <sub>CBO</sub>	Collector-Base Voltage	60	V	
V <sub>CEO</sub>	Collector-Emitter Voltage	40	V	
V <sub>EBO</sub>	Emitter-Base Voltage	6	V	
I <sub>C</sub>	Collector Current	600	mA	
P <sub>C</sub>	Collector Dissipation	350	mW	
T <sub>J,</sub> T <sub>STG</sub>	Operating Junction and Storage Temperature Range	-55 ~ 150	°C	

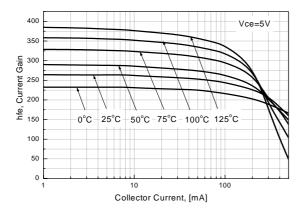
# **Electrical Characteristics** T<sub>a</sub>=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	$I_{\rm C} = 100 \mu {\rm A}, I_{\rm E} = 0$	60		V
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage *	$I_{\rm C} = 1.0 {\rm mA}, I_{\rm B} = 0$	40		V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	$I_{\rm E} = 100 \mu A, I_{\rm C} = 0$	6		V
I <sub>BEV</sub>	Base Cut-off Current	V <sub>CE</sub> = 35V, V <sub>EB</sub> = 0.4V		100	nA
I <sub>CEX</sub>	Collector Cut-off Current	$V_{CE} = 35V, V_{EB} = 0.4V$		100	nA
h <sub>FE</sub>	DC Current Gain *	$ \begin{array}{l} V_{CE} = 1V, \ I_{C} = 0.1 mA \\ V_{CE} = 1V, \ I_{C} = 1 mA \\ V_{CE} = 1V, \ I_{C} = 10 mA \\ V_{CE} = 1V, \ I_{C} = 150 mA \\ V_{CE} = 2V, \ I_{C} = 500 mA \end{array} $	20 40 80 100 40	300	
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage *	$I_{C} = 150$ mA, $I_{B} = 15$ mA $I_{C} = 500$ mA, $I_{B} = 50$ mA		0.4 0.75	V V
V <sub>BE</sub> (sat)	Base-Emitter Saturation Voltage *	$I_{C}$ = 150mA, $I_{B}$ = 15mA $I_{C}$ = 500mA, $I_{B}$ = 50mA	0.75	0.95 1.2	V V
f <sub>T</sub>	Current Gain Bandwidth Product	I <sub>C</sub> = 20mA, V <sub>CE</sub> = 10V, f = 100MHz	250		MHz
C <sub>ob</sub>	Output Capacitance	V <sub>CB</sub> =5V, I <sub>E</sub> =0, f=100KHz		6.5	pF
t <sub>ON</sub>	Turn On Time	$V_{CC} = 30V, V_{BE} = 2V$ $I_{C} = 150mA, I_{B1} = 15mA$		35	ns
t <sub>OFF</sub>	Turn Off Time	$V_{CC} = 30V, I_C = 150mA$ $I_{B1} = I_{B2} = 15mA$		255	ns

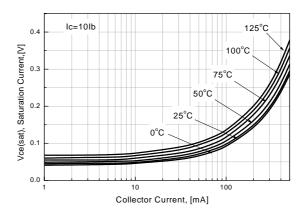
\* Pulse Test: Pulse Width ${\leq}300\mu\text{s},$  Duty Cycle ${\leq}2\%$ 

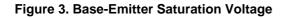
# **Typical Performance Characteristics**

## Figure 1. DC current Gain



## Figure 2. Collector-Emitter Saturation Voltage





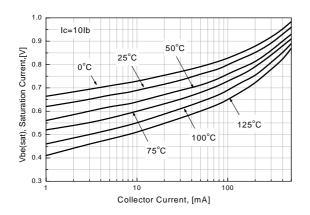


Figure 5. Collector-Base Capacitance

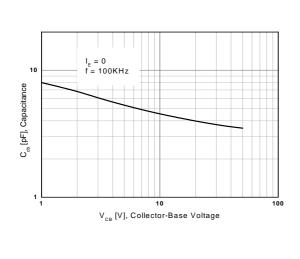
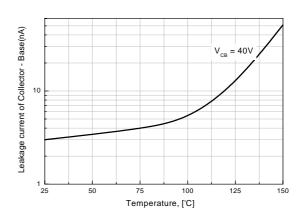
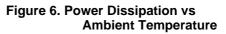
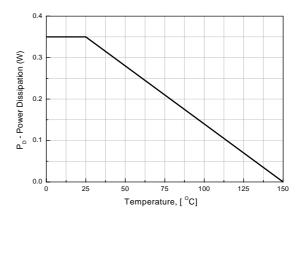
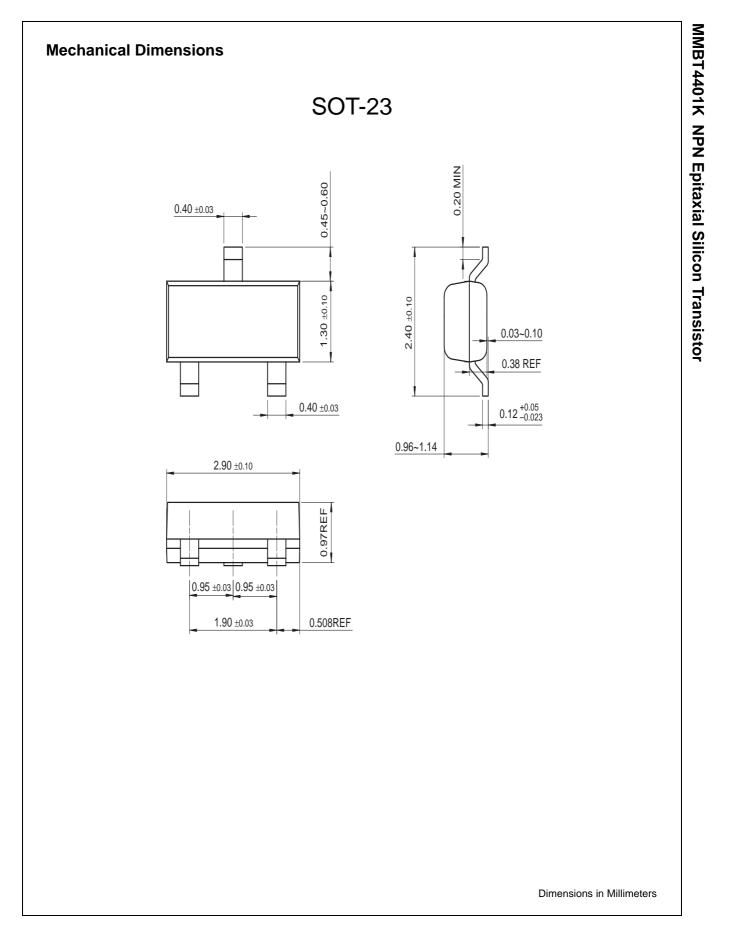


Figure 4. Collector - Base Leakage Current









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